

Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

1-9. (Cancelled)

10. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming a first wiring on a same layer as a source electrode and a [[or]] drain electrode over a substrate;

forming an insulating film over the first wiring;

forming a plurality of contact holes in the insulating film;

forming a second wiring over the insulating film; and

electrically connecting a flat cable to the second wiring to supply signals to the semiconductor device through the second wiring,

wherein the first wiring is in contact with the second wiring via the plurality of contact holes, and

wherein the first wiring extends in parallel with the second wiring.

11. (Previously Presented) A method of manufacturing a semiconductor device according to claim 10, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

12. (Previously Presented) A method of manufacturing a semiconductor device according to claim 10, wherein the first wiring comprises aluminum.

13. (Previously Presented) A method of manufacturing a semiconductor device according to claim 10, wherein the insulating film comprises an interlayer insulating film.

14. (Previously Presented) A method of manufacturing a semiconductor device according to claim 10, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.

15. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming a plurality of gate lines over a substrate;

forming a first insulating film over the plurality of gate lines;

forming a first wiring on a same layer as a source electrode and a [[or]] drain electrode over the first insulating film;

forming a second insulating film over the first wiring;

forming a plurality of contact holes in the second insulating film; and

forming a second wiring over the second insulating film,

wherein the first wiring is in contact with the second wiring via the plurality of contact holes,

wherein the first wiring extends in parallel with the second wiring, [[and]]

wherein the first wiring and the second wiring intersect the plurality of gate lines, and

wherein the first wiring and the second wiring extend along a sideline of a display section.

16. (Previously Presented) A method of manufacturing a semiconductor device according to claim 15, wherein the first insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

17. (Previously Presented) A method of manufacturing a semiconductor device according to claim 15, wherein the first wiring comprises aluminum.

18. (Previously Presented) A method of manufacturing a semiconductor device according to claim 15, wherein each of the first insulating film and the second insulating film comprises an interlayer insulating film.

19. (Previously Presented) A method of manufacturing a semiconductor device according to claim 15, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.

20. (Previously Presented) A method of manufacturing a semiconductor device comprising:

- forming a first wiring and a third wiring in a driving circuit over a substrate;
- forming an insulating film over the first wiring and the third wiring;
- forming a plurality of contact holes in the insulating film;
- forming a second wiring in the driving circuit over the insulating film; and
- electrically connecting a flat cable to the second wiring to supply signals to the semiconductor device through the second wiring,

wherein the first wiring is in contact with the second wiring via the plurality of contact holes,

wherein the first wiring extends in parallel with the second wiring, and
wherein the second wiring intersects with the third wiring.

21. (Previously Presented) A method of manufacturing a semiconductor device according to claim 20, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

22. (Previously Presented) A method of manufacturing a semiconductor device according to claim 20, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

23. (Previously Presented) A method of manufacturing a semiconductor device according to claim 20, wherein the second wiring comprises aluminum.

24. (Previously Presented) A method of manufacturing a semiconductor device according to claim 20, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.

25. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming a first wiring and a third wiring in a driving circuit on a same layer as a gate electrode over a substrate;

forming an insulating film over the first wiring, the third wiring and the gate electrode;

forming a plurality of contact holes in the insulating film; and

forming a second wiring in the driving circuit on a same layer as a source electrode and a [[or]] drain electrode over the insulating film,

wherin the first wiring is in contact with the second wiring via the plurality of contact holes,

wherin the first wiring extends in parallel with the second wiring, and

wherin the second wiring intersects with the third wiring.

26. (Previously Presented) A method of manufacturing a semiconductor device according to claim 25, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

27. (Previously Presented) A method of manufacturing a semiconductor device according to claim 25, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

28. (Previously Presented) A method of manufacturing a semiconductor device according to claim 25, wherein the second wiring comprises aluminum.

29. (Previously Presented) A method of manufacturing a semiconductor device according to claim 25, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.

30. (Previously Presented) A method of manufacturing a semiconductor device comprising:

forming a first wiring and a third wiring in a source line driving circuit over a substrate;
forming an insulating film over the first wiring and the third wiring;
forming a plurality of contact holes in the insulating film;
forming a second wiring in the source line driving circuit over the insulating film; and
electrically connecting a flat cable to the second wiring to supply signals to the semiconductor device through the second wiring,

wherein the first wiring is in contact with the second wiring via the plurality of contact holes,

wherein the first wiring extends in parallel with the second wiring, and
wherein the second wiring intersects with the third wiring.

31. (Previously Presented) A method of manufacturing a semiconductor device according to claim 30, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

32. (Previously Presented) A method of manufacturing a semiconductor device according to claim 30, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

33. (Previously Presented) A method of manufacturing a semiconductor device according to claim 30, wherein the second wiring comprises aluminum.

34. (Previously Presented) A method of manufacturing a semiconductor device according to claim 30, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.

35. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming a first wiring and a third wiring in a source line driving circuit on a same layer as a gate electrode over a substrate;

forming an insulating film over the first wiring, the third wiring and the gate electrode;

forming a plurality of contact holes in the insulating film; and

forming a second wiring in the source line driving circuit on a same layer as a source electrode and a [[or]] drain electrode over the insulating film,

wherein the first wiring is in contact with the second wiring via the plurality of contact holes,

wherein the first wiring extends in parallel with the second wiring, and

wherein the second wiring intersects with the third wiring.

36. (Previously Presented) A method of manufacturing a semiconductor device according to claim 35, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

37. (Previously Presented) A method of manufacturing a semiconductor device according to claim 35, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

38. (Previously Presented) A method of manufacturing a semiconductor device according to claim 35, wherein the second wiring comprises aluminum.

39. (Previously Presented) A method of manufacturing a semiconductor device according to claim 35, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.

40. (Canceled)

41. (Previously Presented) A method of manufacturing a semiconductor device according to claim 15, further comprising forming a plurality of contact holes in the first insulating film, wherein the first wiring is in contact with the plurality of gate lines via the plurality of contact holes in the first insulating film.

42. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming a plurality of gate lines and a first wiring over the substrate;

forming a first insulating film over the first wiring;

forming a first plurality of contact holes in the first insulating film;

forming a second wiring on a same layer as a source electrode and a [[or]] drain electrode over the first insulating film;

forming a second insulating film over the second wiring;

forming a second plurality of contact holes in the second insulating film; and

forming a third wiring over the second insulating film,

wherein the first wiring is in contact with the second wiring via the first plurality of contact holes,

wherein the third wiring is in contact with the second wiring via the second plurality of contact holes, and

wherein the second and third wirings intersect the plurality of gate lines.

43.(New) A method of manufacturing a semiconductor device according to claim 10, wherein a frequency of the signals is more than 1 MHz.

44.(New) A method of manufacturing a semiconductor device according to claim 15, wherein a signal is applied to the second wiring.

45.(New) A method of manufacturing a semiconductor device according to claim 44, wherein a frequency of the signal is more than 1 MHz.

46.(New) A method of manufacturing a semiconductor device according to claim 20, wherein a frequency of the signals is more than 1 MHz.

47.(New) A method of manufacturing a semiconductor device according to claim 25, wherein a signal is applied to the second wiring.

48.(New) A method of manufacturing a semiconductor device according to claim 47, wherein a frequency of the signal is more than 1 MHz.

49.(New) A method of manufacturing a semiconductor device according to claim 30, wherein a frequency of the signals is more than 1 MHz.

50.(New) A method of manufacturing a semiconductor device according to claim 35, wherein a signal is applied to the second wiring.

51.(New) A method of manufacturing a semiconductor device according to claim 50, wherein a frequency of the signal is more than 1 MHz.

52.(New) A method of manufacturing a semiconductor device according to claim 42, wherein a signal is applied to the third wiring.

53.(New) A method of manufacturing a semiconductor device according to claim 52, wherein a frequency of the signal is more than 1 MHz.

54.(New) A method of manufacturing a semiconductor device according to claim 10, wherein a length of at least one of the first wiring and the second wiring is more than 1 cm.

55.(New) A method of manufacturing a semiconductor device according to claim 15, wherein a length of at least one of the first wiring and the second wiring is more than 1 cm.

56.(New) A method of manufacturing a semiconductor device according to claim 20, wherein a length of at least one of the first wiring and the second wiring is more than 1 cm.

57.(New) A method of manufacturing a semiconductor device according to claim 25, wherein a length of at least one of the first wiring and the second wiring is more than 1 cm.

58.(New) A method of manufacturing a semiconductor device according to claim 30, wherein a length of at least one of the first wiring and the second wiring is more than 1 cm.

59.(New) A method of manufacturing a semiconductor device according to claim 35, wherein a length of at least one of the first wiring and the second wiring is more than 1 cm.

60.(New) A method of manufacturing a semiconductor device according to claim 42, wherein a length of at least one of the first wiring, the second wiring and the third wiring is more than 1 cm.

61.(New) A method of manufacturing a semiconductor device according to claim 10, wherein the first wiring and the second wiring are provided in a driver circuit which drives a display section.

62.(New) A method of manufacturing a semiconductor device according to claim 15, wherein the first wiring and the second wiring are provided in a driver circuit which drives the display section.

63.(New) A method of manufacturing a semiconductor device according to claim 42, wherein the first wiring, the second wiring and the third wiring are provided in a driver circuit which drives a display section.

64.(New) A method of manufacturing a semiconductor device according to claim 20, wherein the third wiring is narrower than the second wiring.

65.(New) A method of manufacturing a semiconductor device according to claim 25, wherein the third wiring is narrower than the second wiring.

66.(New) A method of manufacturing a semiconductor device according to claim 30, wherein the third wiring is narrower than the second wiring.

67.(New) A method of manufacturing a semiconductor device according to claim 35, wherein the third wiring is narrower than the second wiring.